

Class	Subclass
ISSUE CLASSIFICATION	

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PATENT NUMBER

U.S. **UTILITY** Patent Application

<p>O.I.P.E.</p> <p>7A SCANNED <u>KSO</u> Q.A. <u>AA</u></p>	<p>PATENT DATE</p>
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APPLICATION NO. 09/995575	CONT/PRIOR F	CLASS 438	SUBCLASS	ART UNIT 281 2813	EXAMINER
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APPLICANTS

Tamihide Yasumoto:

TITLE

Semiconductor device manufacturing method using metal silicide
reaction after ion implantation
silicon wiring

PTO-2040
12/99

ISSUING CLASSIFICATION												
ORIGINAL				CROSS REFERENCE(S)								
CLASS		SUBCLASS		CLASS	SUBCLASS (ONE SUBCLASS PER BLOCK)							
INTERNATIONAL CLASSIFICATION												

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<input type="checkbox"/> TERMINAL DISCLAIMER	DRAWINGS		CLAIMS ALLOWED	
	Sheets Drwg.	Figs. Drwg.	Print Fig.	Total Claims
<input checked="" type="checkbox"/> The term of this patent subsequent to _____ (date) has been disclaimed.	_____ (Assistant Examiner) _____ (Date)		NOTICE OF ALLOWANCE MAILED	
<input type="checkbox"/> The term of this patent shall not extend beyond the expiration date of U.S Patent. No. _____	_____ (Primary Examiner) _____ (Date)		ISSUE FEE	
			Amount Due	Date Paid
<input type="checkbox"/> The terminal _____ months of this patent have been disclaimed.	_____ (Legal Instruments Examiner) _____ (Date)		ISSUE BATCH NUMBER	

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